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PTO/SB/30 (10-01)

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# REQUEST FOR CONTINUED EXAMINATION (RCE) TRANSMITTAL

Address to: Commissioner for Patents BOX RCE Washington, DC 20231

Application No.	09/600,546	A
Filing Date	July 12, 2000	~
First Named Inventor	Claude Chappert	· PN
Group Art Unit	1756	
Examiner Name	Angebranndt, M.J.	٦.
Attorney Docket Number	15675P322	7

This is a Request for Continued Examination (RCE) under 37 C.F.R. § 1.114 of the above-identified application.  Request for Continued Examination (RCE) practice under 37 CFR § 1.114 does not apply to any utility or plant application filed prior to June 8, 1995,				
or to any design application. See Instruction Sheet for RCEs (not to be submitted to the USPTO) on page 2				
1.	1. Submission required under 37 C.F.R. § 1.114			
	<ul> <li>a.</li></ul>			
	ii. ☐ Consider the arguments in the Appeal Brief or Reply Brief previously filed on iii. ☐ Other			
	b. ⊠ Enclosed i. □ Amendment/Reply	iii.		
	ii.	iv. Dither Preliminary Amendment		
2.	2. Miscellaneous			
	a. Suspension of action on the above-identified application is requested under 37 C.F.R. § 1.103(c) for a period of months. (Period of suspension shall not exceed 3 months; Fee under 37 C.F.R. § 1.17(i) required)			
	b. D Other	<del></del>		
3.	Fees The RCE fee under 37 C.F.R. § 1.17(e) is require	d by 37 C.F.R. § 1.114 when the RCE is filed.		
	The Director is hereby authorized to charge the following fees, or credit any overpayments, to Deposit Account No. <u>02-2666</u> .			
	i. RCE fee required under 37 C.F.R. § 1.17(e)			
	ii.			
	b.  Check in the amount of \$1,680.00 enclosed			
	c. Payment by credit card (Form PTO-2038 enclosd)			
WARNING: Information on this form may become public. Credit card information should not be included on this form. Provide credit card information and authorization on PTO-2038.				
SIGNATURE OF APPLICANT, ATTORNEY, OR AGENT REQUIRED				
Nar	me (Print/Type) Walter T. Kim	Registration No. (Attorney/Agent) 42,731		
Signature Date January 8, 2003				
$\subseteq$	CERTIFICATE (	OF MAILING OR TRANSMISSION		
I hereby certify that this correspondence is being deposited with the United States Postal Service as First Class mail with sufficient postage in an envelope addressed to: Box RCE, Assistant Commissioner for Patents, Washington, D.C. 20231 on:  January 8, 2003				
Nar	Name (Print/Type) Linda D'Ælia			
Sig	gnature Starts Start	Date January 8, 2003		

Burden Hour Statement: This form is estimated to take 0.2 hours to complete. Time will vary depending upon the needs of the individual case. Any comments on the amount of time you are required to complete this form should be sent to the Chief Information Officer, U.S. Patent and Trademark Office, Washington, DC 20231. DO NOT SEND FEES OR COMPLETED FORMS TO THIS ADDRESS. SEND TO: Commissioner for Patents, Box RCE, Washington, DC 20231.

101/15/2003 CV0111 00000144 09600546

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Attorney Docket No. 015675.P322

# IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

In re the Patent Application of:

**CLAUDE CHAPPERT** 

Serial No. 09/600,546

Filed: July 12, 2000

For: MAGNETIC ETCHING PROCESS, ESPECIALLY FOR MAGNETIC OR

MAGNETOOPTIC RECORDING

Examiner: Angebranndt, Martin J.

Art Unit: 1756



## PRELIMINARY AMENDMENT

Box RCE Commissioner for Patents Washington, D.C. 20231-9998

Dear Sir:

In connection with the RCE (Request for Continued Examination) filed herewith regarding the above-referenced application, Applicant respectfully requests consideration of the following amendments and remarks.

### **IN THE CLAIMS**

#### Please amend Claim 1 as follows:

1. (Amended) A writing process for forming a pattern on a multi-layer material composed of thin layers deposited on a substrate, in which said multi-layer material is irradiated by means of a beam of light ions, having an energy of the order of or less than a hundred keV, wherein one or more regions of the multi-layer material having individual sizes of the order of 1 micrometer or less are selectively irradiated, the irradiation dose being controlled so as to be a few 10<sup>16</sup> ions/cm<sup>2</sup> or less, the irradiation